

SSR6010M
SSR6010Z

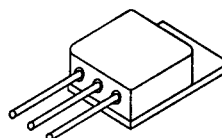
Designer's Data Sheet

FEATURES:

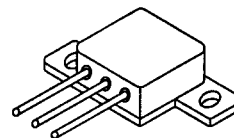
- Low Reverse Leakage
- Low Forward Voltage Drop
- Guard Ring for Overvoltage protection
- Isolated Hermetically Sealed Power Package
- Ceramic Seals for Improved Hermeticity
- Custom Lead Forming Available
- Eutectic Die Attach
- 175°C Operating Temperature
- TX, TXV and Space Level Screening Available

60 AMP
100 VOLTS
SCHOTTKY
RECTIFIER

TO-254



TO-254Z



MAXIMUM RATINGS

RATING	SYMBOL	VALUE	UNIT
Peak Repetitive Reverse and DC Blocking Voltage	VRRM VRWM VR	100	Volts
Average Rectified Forward Current (Resistive Load, 60Hz, Sine Wave, TA=25°C)	Io	60	Amps
Peak Surge Current (8.3 ms Pulse, Half Sine Wave Superimposed on Io, allow junction to reach equilibrium between pulses, TA=25°C)	IFSM	500	Amps
Operating and storage temperature	Top & Tstg	-55 to +175	°C
Maximum Thermal Resistance Junction to Case	RθJC	0.80	°C/W

Available with Glass or Ceramic Seals. Contact Factory for Details.

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PRELIMINARY

SSDI
SOLID STATE DEVICES, INC

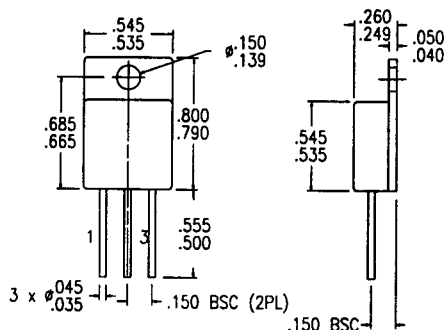
14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	MAXIMUM	UNIT
Instantaneous Forward Voltage Drop (IF = 30 Adc, TA=25°C, 300μs Pulse) (IF = 60 Adc, TA=25°C, 300μs Pulse)	VF1	0.9 1.2	Vdc
Instantaneous Forward Voltage Drop (IF=30 Adc, TA= -125°C, 300μs Pulse)	VF2	0.75	Vdc
Reverse Leakage Current (Rated VR, TA=25°C, 300μs pulse minimum)	IR1	12	mA
Reverse Leakage Current (Rated VR, TA=125°C, 300μs pulse minimum)	IR2	30	mA
Junction Capacitance (VR = 5 Vdc, TA=25°C, f= 1 MHz)	CJ	1600	pf

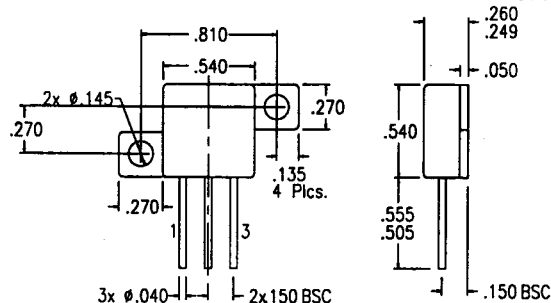
CASE OUTLINE: TO-254

PIN OUT:
PIN 1: CATHODE
PIN 2: ANODE
PIN 3: ANODE



CASE OUTLINE: TO-254Z

PIN OUT:
PIN 1: CATHODE
PIN 2: ANODE
PIN 3: ANODE



TYPICAL OPERATING CURVES

(TA=25°C Unless otherwise specified)

